



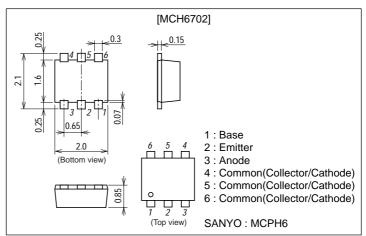
DC/DC Converter Applications

Features

- Composite type with a PNP transistor and a Schottky barrier diode contained in one package facilitatiing high-density mounting.
- The MCH6702 consists of two chips which are equivalent to the MCH6101 and SBS006, respectively.
- The ultrasmall package facilitates miniaturization in end products. (mounting height 0.85mm).

Package Dimensions

unit : mm 2191A



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
[TR]	•			
Collector-to-Base Voltage	VCBO		-15	V
Collector-to-Emitter Voltage	VCEO		-15	V
Emitter-to-Base Voltage	VEBO		-5	V
Collector Current	IC		-1.5	Α
Collector Current (Pulse)	ICP		-3	Α
Base Current	lΒ		-300	mA
Collector Dissipation	PC	Mounted on a ceramic board(600mm ² X0.8mm)	1.0	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +125	°C
[SBD]				
Repetitive Peak Reverse Voltage	VRRM		30	V
Non-repetitive Peak Reverse Surge Voltage	VRSM		30	V
Average Output Current	IO		0.7	Α
Surge Current	IFSM	50Hz sine wave, 1 cycle	10	Α
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	°C

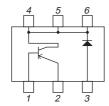
Marking: PB

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Electrical Characteristics at Ta=25°C

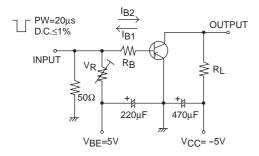
Parameter	Cymahal	Conditions	Rathings			11.2
	Symbol		min	typ	max	Unit
[TR]						
Collector Cutoff Current	ICBO	V _{CB} =-12V, I _E =0			-0.1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =-4V, I _C =0			-0.1	μΑ
DC Current Gain	hFE	V _{CE} =-2V, I _C =-100mA	200		560	
Gain-Bandwidth Product	fŢ	VCE=-2V, IC=-300mA		350		MHz
Output Capacitance	Cob	V _{CB} =-10V, f=1MHz		17		pF
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C =-750mA, I _B =-15mA		-120	-180	mV
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =-750mA, I _B =-15mA		-0.85	-1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =-10μA, I _E =0	-15			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =-1mA, R _{BE} =∞	-15			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =-10μA, I _C =0	-5			V
Turn-ON Time	ton	See specified Test Circuit		50		ns
Storage Time	t _{stg}	See specified Test Circuit		90		ns
Fall Time	tf	See specified Test Circuit		15		ns
[Di]						
Reverse Voltage	٧R	I _R =0.5mA	30			V
Forward Voltage	V _F 1	I _F =0.3A		0.35	0.40	V
	V _F 2	I _F =0.5A		0.42	0.47	V
	VF3	I _F =0.7A		0.5	0.55	V
Reverse Current	IR	V _R =10V			200	μΑ
Interterminal Capacitance	С	V _R =10V, f=1MHz		20		pF
Reverse Recovery Time	t _{rr}	I _F =I _R =100mA, See specified Test Circuit			10	ns

Electrical Connection



Switching Time Test Circuit

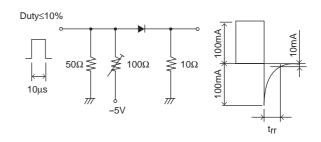
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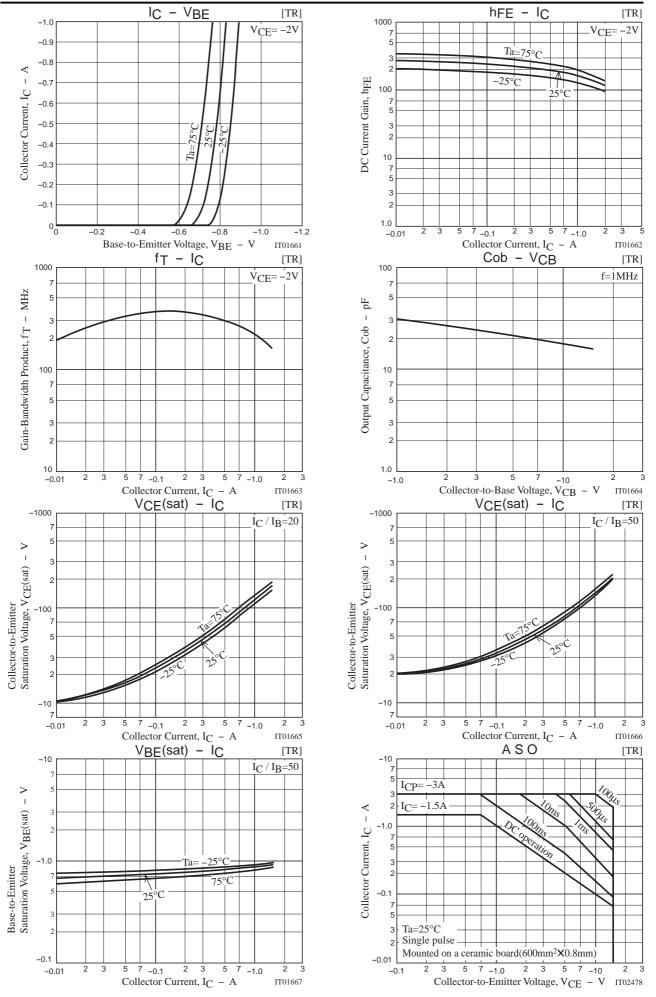
 $I_{C} = -20I_{B1} = 20I_{B2} = -750mA$

trr Specified Circuit

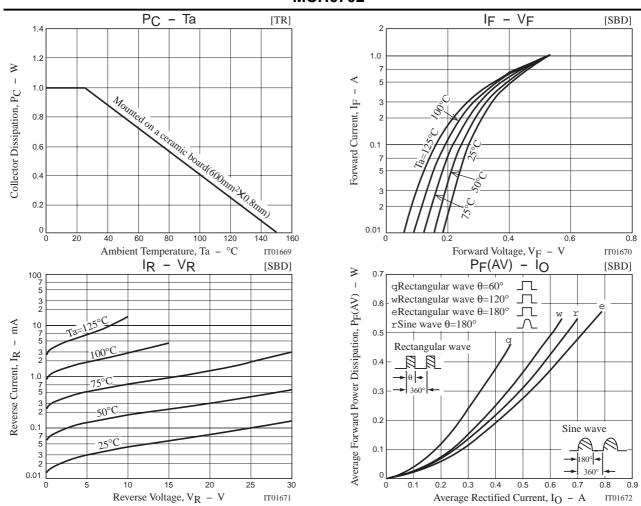
[Di]



MCH6702



MCH6702



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